WEST Search History

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DATE: Monday, December 05, 2005

Hide?	Set Name	Query	Hit Count
	DB=PGPB,USPT,EPAB,JPAB,DWPI; THES=ASSIGNEE; PLUR=YES; OP=ADJ		
☐	L1	host.clm. and dopant.clm. and powder.clm.	31
☐	L2	L1 and melt$4.clm.	4
☐	L3	host same dopant same melt$4 same container	5

END OF SEARCH HISTORY

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DATE: Monday, December 05, 2005

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	DB=PGPB,USPT,EPAB,JPAB,DWPI; THES=ASSIGNEE; PLUR=YES; OP=ADJ		
☐	L1	host.clm. and dopant.clm. and powder.clm.	31
☐	L2	L1 and melt$4.clm.	4
☐	L3	host same dopant same melt$4 same container	5
☐	L4	5242531.pn.	2

END OF SEARCH HISTORY

L3: Entry 3 of 5 File: USPT Jul 3, 2001

DOCUMENT-IDENTIFIER: US 6254674 B1
TITLE: Method of controllably delivering dopant by limiting the release rate of dopant from a submerged vessel

Brief Summary Text (8):
U.S. Pat. No. 5,242,531 to Klingshirn et al. discloses a process for continuously recharging a melt crucible with additional molten host material and additional molten dopant. In this regard, the Klingshirn '531 et al. patent describes separate containers filled with the host material and the dopant that are positioned above the melt crucible. Feedlines connect the containers with an additional crucible or container in which the host material and the dopant are mixed and melted. This additional crucible includes an outlet for supplying additional molten semiconductor material to the melt in order to recharge the melt during the crystal-growing process. While the '531 Klingshirn et al. patent addresses some of the issues with respect to controlling the amount of dopant in the melt throughout the course of a crystal-growing process, the technique described by the '531 Kingshirn et al. patent requires multiple containers positioned above the melt crucible which may complicate the design of the crystal-growing furnace and limit access to the melt crucible during the crystal-growing process.

L3: Entry 4 of 5 File: USPT Jan 30, 2001

DOCUMENT-IDENTIFIER: US 6179914 B1
TITLE: Dopant delivery system and method

Brief Summary Text (8):
U.S. Pat. No. 5,242,531 to Klingshirn et al. discloses a process for continuously recharging a melt crucible with additional molten host material and additional molten dopant. In this regard, the Klingshirn '531 et al. patent describes separate containers filled with the host material and the dopant that are positioned above the melt crucible. Feedlines connect the containers with an additional crucible or container in which the host material and the dopant are mixed and melted. This additional crucible includes an outlet for supplying additional molten semiconductor material to the melt in order to recharge the melt during the crystal-growing process. While the '531 Klingshirn et al. patent addresses some of the issues with respect to controlling the amount of dopant in the melt throughout the course of a crystal-growing process, the technique described by the '531 Kingshirn et al. patent requires multiple containers positioned above the melt crucible which may complicate the design of the crystal-growing furnace and limit access to the melt crucible during the crystal-growing process.

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DATE: Friday, December 02, 2005

Hide?	Set Name	Query	Hit Count
		DB=PGPB,USPT,EPAB,JPAB,DWPI; THES=ASSIGNEE; PLUR=YES; OP=ADJ	
☐	L1	264/112.ccls. and 264/308.ccls.	8
☐	L2	264/113.ccls. and 264/308.ccls.	38
☐	L3	264/113.ccls. and 264/401.ccls.	17
☐	L4	264/112.ccls. and 264/401.ccls.	2
☐	L5	L1 and binder.clm.	3
☐	L6	L2 and binder.clm.	13
☐	L7	L3 and binder.clm.	5
☐	L8	L4 and binder.clm.	1
☐	L9	6733528.pn. and activation agent	0
☐	L10	6403002.pn. and activation agent	0
☐	L11	6322728.pn. and activation agent	0
☐	L12	6322728.pn. and (acid or amine or alcohol or ketone or salt)	1
☐	L13	6733528.pn. and (acid or amine or alcohol or ketone or salt)	1
☐	L14	6403002.pn. and (acid or amine or alcohol or ketone or salt)	1
☐	L15	hochsmann.IN. and activation agent	2
☐	L16	ederer.IN. and activation agent	3
☐	L17	ghosh.IN. host.clm. and dopant.clm.	0
☐	L18	ghosh.IN. and host.clm. and dopant.clm.	12
☐	L19	carlton.IN. and host.clm. and dopant.clm.	14
☐	L20	hatwar.IN. and host.clm. and dopant.clm.	31
☐	L21	L20 and seal$4.clm.	2
☐	L22	L19 and seal$4.clm.	2
☐	L23	L18 and seal$4.clm.	2

END OF SEARCH HISTORY